DECLARATION FOR PATENT APPLICATION Docket No. NECW 18.159

As a below named inventor, I hereby declare that:

My residence, post office address	and citizenship are as stated bel	ow next to my name.		
(if plural names are listed below tion entitled MANUFACTURING MET) of the subject matter which is THOD OF SEMICONDUCTOR INTEGRA	ne is listed below) or an original, fir claimed and for which a patent is s MTED CIRCUIT INCLUDING SIMULTAN FILM AND SEMICONDUCTOR INTEGRA	ought on the inven- EOUS FORMATION OF VIA HC	
the specification of which			ANUFACTURING METHOD	
(check one) [X] is attached he [] was filed on				
Application S	Serial No			
and was ame	nded on		(if applicable).	
hereby state that I have revie		its of the above identified specific	ation, including the	
acknowledge the duty to discle with Title 37, Code of Federal R		al to the examination of this application	cation in accordance	
or inventor's certificate listed b		tates Code, §119 of any foreign app below any foreign application for thich priority is claimed:		
Prior Foreign Application(s)	Japan	18/01/2000	Priority Claimed Yes Xxo x	
(Number)	(Country)	(Day/Month/Year Filed)	37 37	
(Number)	(Country)	(Day/Month/Year Filed)	_ Yes No	
(Number)	(Country)	(Day/Month/Year Filed)	_ Ycs No	
rtion of the at the officers	. Title 25 Their 4 Cours Code St	.20 of any United States application	(a) listed below and	
(Application Serial No.)	(Filing Date)	(Status - patented, pe	(Status - patented, pending, abandoned)	
(Application Serial No.)	(Filing Date)	(Status - patented, po	ending, abandoned)	
		eg. No. 18,923, Samson Helfgott, and to transact all business in the I		
Address all correspondence to:	HELFGOTT & KAR 60th Floor	AS P.C.		
	Empire State Buil			
•	New York, New York 1 Telephone No. (212)			
tion and belief are believed to statements and the like so mad	ents made herein of my own kno be true; and further that these sta e are punishable by fine or imp	owledge are true and that all statements were made with the knowledge risonment, or both, under Section 1 y jeopardize the validity of the appropriate the section 1 the s	edge that willful false OD1 of Title 18 of the	
Full name of sole or first inven	tor ATSUSHI NISHIZ			
Inventor's signature	Atsushi nushig	Date Decer	mber 15, 2000	
Residence Tokyo, Jap	pan		Japanese	
Post Office Addressc/o	NEC Corporation,	7-1, Shiba 5-chome, N		
Full name of second joint inve	• • • • • • • • • • • • • • • • • • • •	Data		
	Second Inventor's signature		1.1	
Kesidence		Citizenship		
Past Office Address				

THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: Atsushi NISHIZAWA

Filed

: Concurrently herewith

For

: MANUFACTURING METHOD OF

Serial No.

: Concurrently herewith

December 29, 2000

Assistant Commissioner of Patents Washington, D.C. 20231

SUB-POWER OF ATTORNEY

S I R:

I, Aaron B. Karas, Reg. No. 18,923 attorney of record herein, do hereby grant a sub-power of attorney to Linda S. Chan, Reg. No. 42,400, Harris A. Wolin, Reg. No. 39,432, Brian S. Myers, Reg. No. 46,947 and Michael Markowitz, Reg. No. 30,659 to act and sign in my behalf in the above-referenced application.

Respectfully submitted,

Aaron B. Karas

Reg. No 18,923

HELFGOTT & KARAS, P.C. 60th FLOOR EMPIRE STATE BUILDING NEW YORK, NY 10118 DOCKET NO.:NECW 18.159 BWU:power

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On: December 29, 2000

By: Brendy Lynn Belony

Any fee due as a result of this paper, not covered by an enclosed check may be charged on Deposit Acct. No. 08-1634..